**LIST OF REFERENCES CITED BY APPLICANT**
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ATTY. DOCKET NO.:

4717-10200

APPLICATION NO.:

10/784,017

APPLICANT:

Bruno GHYSELEN et al.

FILING DATE:

February 20, 2004

GROUP:

2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BHA	AA	2003/0013305 A1	1/2003	Sugii et al.	438	689	
BHA	AB	6,059,895	5/2000	Chu et al.	148	33.1	
BHA	AC	6,100,166	8/2000	Sakaguchi et al.	438	455	
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	AG						
	AI						

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
BHA	AJ	WO02/43153	5/2002	PCT (Abstract)			X	
	AK							
	AL							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)


	AM	
	AN	
	AO	
	AP	
	AQ	

EXAMINER


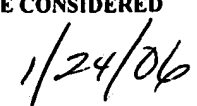
DATE CONSIDERED

1/24/06

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BAA	AA	5,882,987	3/1999	Sirikrishnan	438	458		
	AB	5,906,951	5/1999	Chu et al.	438	751		
	AC	6,524,935	2/2003	Canaperi et al.	438	478		
	AD	6,573,126 B2	6/2003	Cheng et al.	438	149		
	AE	6,633,066 B1	10/2003	Bae et al.	257	347		
	AF	2003/0003679 A1	6/2003	Doyle et al.	438	406		
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
BHA	AJ	EP 1 248 294 A2	10/2002	Europe			X	
	AK	FR 2 818 010 (with English Abstract)	8/2002	France			X	
	AL	DE 101 00 194 A1	6/2001	Germany			X	
	AM	WO 02/15244 A2	2/2002	PCT			X	
	AN	WO 02/47156 A1	2/2002	PCT			X	
	AO	WO 99/53539	10/1999	PCT			X	
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BHA	AP	T. Tezuka et al., XP001109835, High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique, Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002)						
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BHA	AA	5,461,243	10/1995	Ek et al.	257	190	
BHA	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
BHA	AC	2002/0072130	6/2002	Cheng et al.	438	10	
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BHA	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si _{1-x} Ge _x /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)					
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	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.					
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